

/ Revised record

F	2017-4				
G	2019-11-1 1	2	V_{CBO} V_{CEO} V_{EBO} I_{CEO}		
H	2020-5-21	1			
A	2022-2-9	all	BR Q AEC-Q101 H Q 245±5°C 5±0.5sec 255±5°C 5±0.5sec		

BRMMBT5401Q

Rev.A Feb.-2022



SOT-23

PNP

Silicon PNP transistor in a SOT-23 Plastic Package.

, BRMMBT5551Q
High voltage, c

AEC-Q101

BRMMBT5401Q

Rev.A Feb.-2022



DATA SHEET

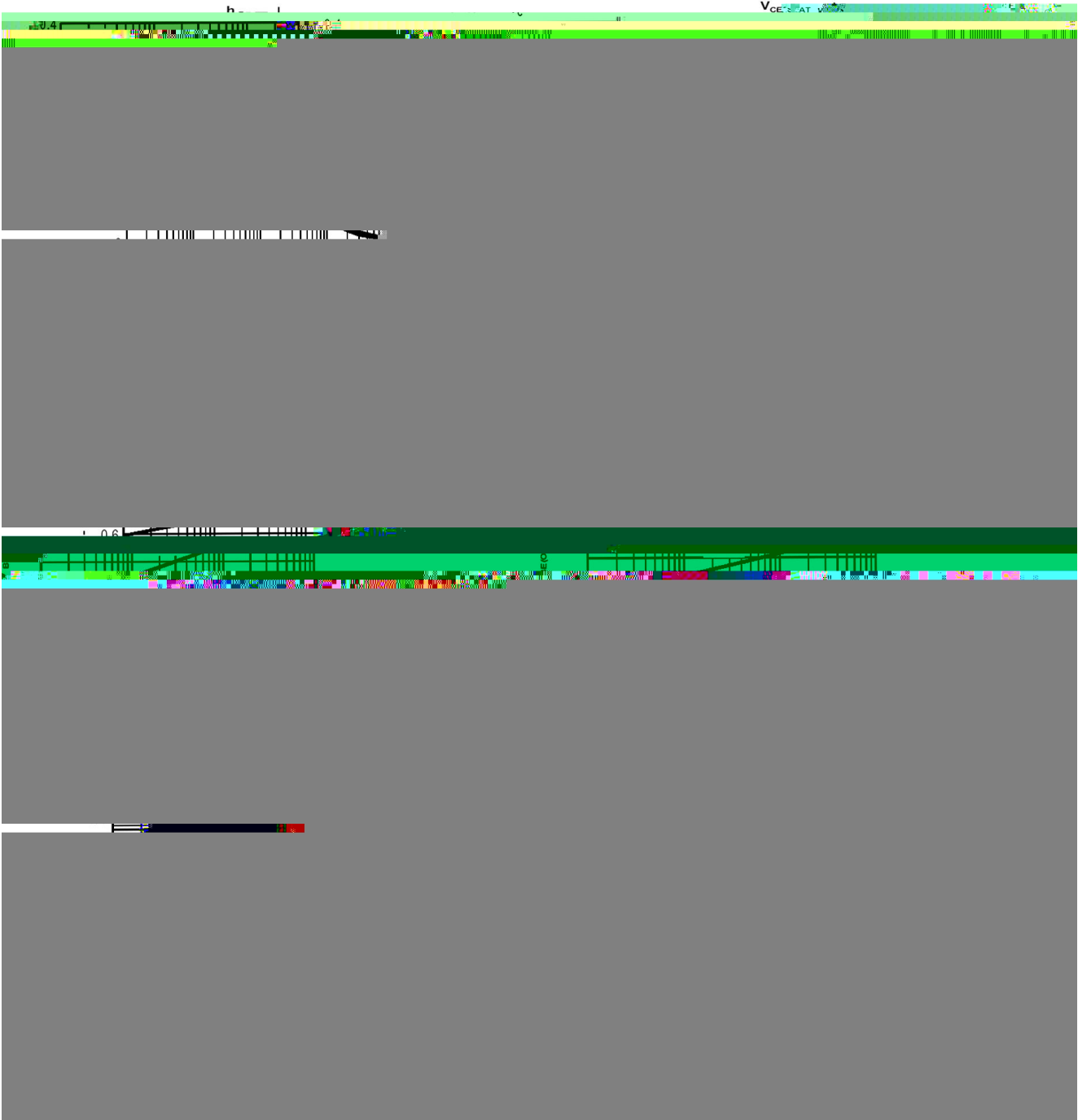
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-180	V
Collector to Emitter Voltage	V_{CEO}	-160	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current	I_C	-600	mA
Base Current	I_B	-300	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}		

Parameter

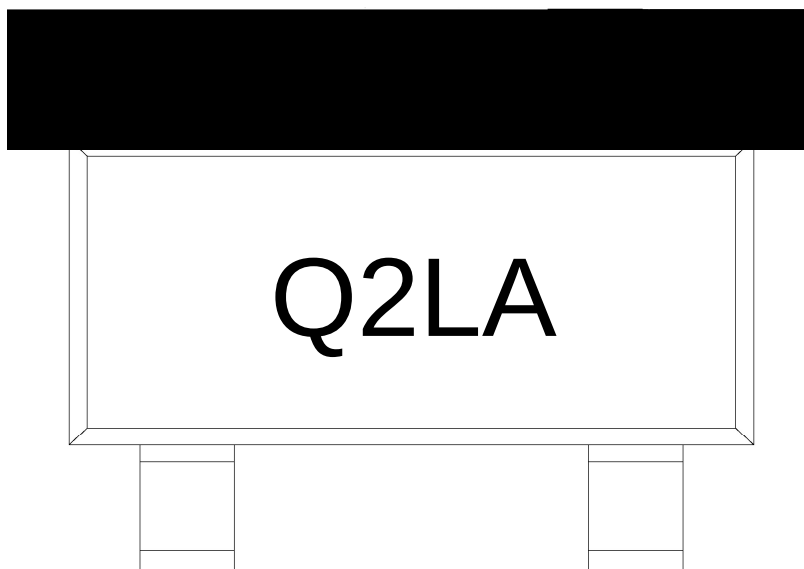
Symbol

Test Conditions

/ Electrical Characteristic Curve



/ Marking Instructions



Q

2L

A h_{FE}

Note:

Q: Automobile halogen-free product Code

2L Product Type Code

A h_{FE} Classifications Symbol Code

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- | | | | | | |
|---|-------|-----|-----------|---------|--|
| 1 | 150 | 200 | 60 | 120sec; | 1.Preheating:150~200°C, Time:60~120sec. |
| 2 | 255±5 | | 5±0.5sec; | | 2.Peak Temp.:255±5°C, Duration:5±0.5sec. |
| 3 | | 2 | 10°C/sec. | | 3. Cooling Speed: 2~10°C/sec. |

/ Resistance to Soldering Heat Test Conditions

260±5°C

10±1 sec.

Temp.:260±5

Time:10±1 sec